



1 GHz, 25 dB gain high output power doubler Rev. 02 — 16 November 2009

Product data sheet

Product profile 1.

1.1 General description

Hybrid amplifier module in a SOT115J package, operating at a supply voltage of 24 V Direct Current (DC), employing Hetero junction Field Effect Transistor (HFET) GaAs dies.



This device is sensitive to ElectroStatic Discharge (ESD). Therefore care should be taken during transport and handling.

1.2 Features

- High output power capability
- Excellent linearity
- Extremely low noise
- Excellent return loss properties
- Rugged construction
- Unconditionally stable
- Thermal optimized design

1.3 Applications

CATV systems operating in the 40 MHz to 1000 MHz frequency range

1.4 Quick reference data

Table 1. **Quick reference data**

Bandwidth to 1000 MHz; V_B = 24 V (DC); T_{mb} = 35 °C; unless otherwise specified.

Symbol	Parameter	Conditions		Тур	Max	Unit
Gp	power gain	f = 45 MHz	-	24.0	-	dB
		f = 1000 MHz	24.0	25.0	26.0	dB
I _{tot}	total current		<u>[1]</u> 430	450	470	mA

[1] Direct Current (DC).



2. Pinning information

Table 2.	Pinning		
	Description		Graphic symbol
1	input		
2, 3	common	13579	5
5	+V _B		$\frac{1}{9}$
7, 8	common		2378
9	output		2 3 7 8 sym095

3. Ordering information

Table 3. Ord	lering inforn Package		
	Name	Description	Version
CGD1044H	-	rectangular single-ended package; aluminium flange; 2 vertical mounting holes; $2 \times 6-32$ UNC and 2 extra horizontal mounting holes; 7 gold-plated in-line leads	SOT115J

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Max	Unit
V _B	supply voltage		-	30	V
V _{i(RF)}	RF input voltage	single tone	-	75	dBmV
T _{stg}	storage temperature		-40	+100	°C
T _{mb}	mounting base temperature)	-20	+100	°C

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5. Characteristics

Table 5. Characteristics

Bandwidth to 1000 MHz; $V_B = 24 V (DC)$; $T_{mb} = 35$ °C; unless otherwise specified.

Symbol	Parameter	Conditions			Тур	Max	Unit
G _p power gain	power gain	f = 45 MHz		-	24.0	-	dB
	f = 1000 MHz		24.0	25.0	26.0	dB	
SL _{sl}	slope straight line	f = 45 MHz to 1000 MHz	[1]	-	1.0	-	dB
FL	flatness of frequency response	f = 45 MHz to 1000 MHz	[2]	-	0.5	-	dB
СТВ	composite triple beat	$V_o = 55 \text{ dBmV}$ at 1000 MHz	[3]	-	-83	-	dBc
		$V_o = 59 \text{ dBmV}$ at 1000 MHz	[3]	-	-75	-70	dBc
CSO	composite second-order distortion	$V_o = 55 \text{ dBmV}$ at 1000 MHz	[3]	-	-80	-	dBc
		$V_o = 59 \text{ dBmV}$ at 1000 MHz	[3]	-	-76	-68	dBc
Xmod	cross modulation	$V_o = 55 \text{ dBmV}$ at 1000 MHz	[3]	-	-75	-	dB
		$V_o = 59 \text{ dBmV}$ at 1000 MHz	[3]	-	-67	-	dB
CCN	CCN carrier-to-composite noise	$V_o = 55 \text{ dBmV}$ at 1000 MHz	[3]	-	65	-	dBc
		$V_o = 59 \text{ dBmV}$ at 1000 MHz	[3]	55	58	-	dBc
RL _{in} i	input return loss	f = 45 MHz to 200 MHz		20.0	-	-	dB
		f = 200 MHz to 550 MHz		17.5	-	-	dB
		f = 550 MHz to 870 MHz		15.0	-	-	dB
		f = 870 MHz to 914 MHz		14.5	-	-	dB
		f = 914 MHz to 1000 MHz		14.0	-	-	dB
RL _{out}	output return loss	f = 45 MHz to 200 MHz		21.0	-	-	dB
		f = 200 MHz to 550 MHz		20.0	-	-	dB
		f = 550 MHz to 870 MHz		18.0	-	-	dB
		f = 870 MHz to 914 MHz		17.5	-	-	dB
		f = 914 MHz to 1000 MHz		17.0	-	-	dB
NF	noise figure	f = 50 MHz to 1000 MHz		-	5.0	5.5	dB
I _{tot}	total current		<u>[4]</u>	430	450	470	mA

[1] G_p at 1000 MHz minus G_p at 45 MHz.

[2] flatness straight line (peak to valley).

[3] 79 NTSC channels + 75 digital channels (-6 dB offset); tilt extrapolated to 18 dB at 1000 MHz.

[4] Direct Current (DC).

CGD1044H

6. Package outline

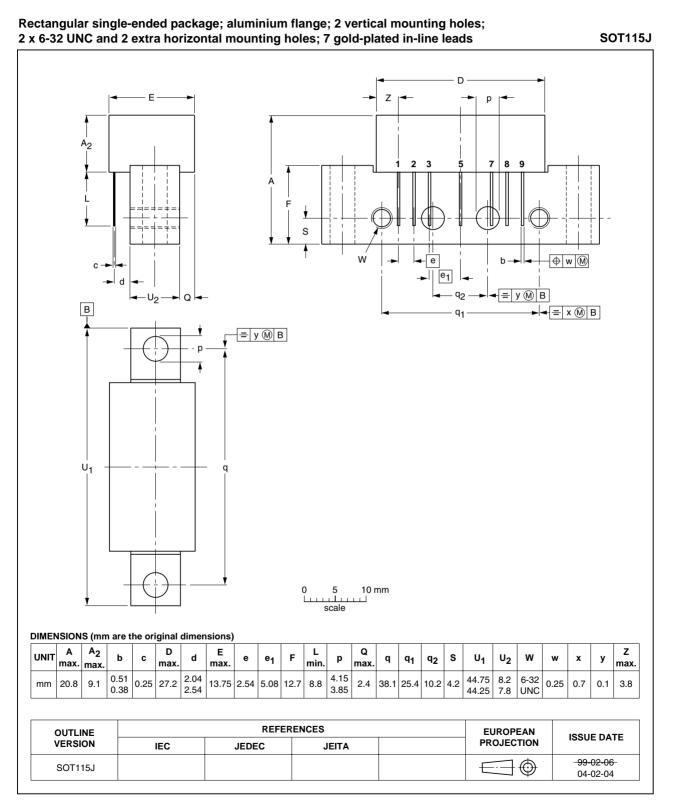


Fig 1. Package outline SOT115J

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7. Abbreviations

Table 6. At	breviations
Acronym	Description
CATV	Community Antenna TeleVision
GaAs	Gallium-Arsenide
NTSC	National Television Standard Committee
RF	Radio Frequency
UNC	UNified Coarse

8. Revision history

Table 7. Revision history					
	Release date	Data sheet status	Change notice	Supersedes	
CGD1044H_2	20091116	Product data sheet	-	CGD1044H_1	
Modifications:	• Table 5 on pa	age 3: Correction made to the u	init of Xmod.		
CGD1044H_1	20071010	Product data sheet	-	-	

9. Legal information

9.1 Data sheet status

Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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